# Power MOSFET 14 Amps, 25 Volts

## **N-Channel DPAK**

### Features

- Planar HD3e Process for Fast Switching Performance
- Low R<sub>DS(on)</sub> to Minimize Conduction Loss
- Low C<sub>iss</sub> to Minimize Driver Loss
- Low Gate Charge
- Optimized for High Side Switching Requirements in High-Efficiency DC-DC Converters
- Pb-Free Packages are Available

MAXIMUM RATINGS (	$T_J = 25^{\circ}C$ unless otherwise specified)
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Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>	25	Vdc
Gate-to-Source Voltage - Continuous	V <sub>GS</sub>	±20	Vdc
$\begin{array}{l} \mbox{Thermal Resistance - Junction-to-Case} \\ \mbox{Total Power Dissipation } @ T_A = 25^{\circ}C \\ \mbox{Drain Current - Continuous } @ T_A = 25^{\circ}C, \mbox{Chip} \\ \mbox{- Continuous } @ T_A = 25^{\circ}C, \mbox{Limited by Package} \\ \mbox{- Single Pulse (tp \leq 10 \ \mu s) \end{array}$	R <sub>0JC</sub> PD ID ID	6.0 20.8 14 11.4 28	°C/W W A A A
Thermal Resistance, Junction-to-Ambient (Note 1) Total Power Dissipation @ $T_A = 25^{\circ}C$ Drain Current - Continuous @ $T_A = 25^{\circ}C$	R <sub>θJA</sub> P <sub>D</sub> I <sub>D</sub>	80 1.56 3.1	°C/W W A
Thermal Resistance, Junction-to-Ambient (Note 2) Total Power Dissipation @ $T_A = 25^{\circ}C$ Drain Current - Continuous @ $T_A = 25^{\circ}C$	R <sub>θJA</sub> P <sub>D</sub> I <sub>D</sub>	120 1.04 2.5	°C/W W A
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	ΤL	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. When surface mounted to an FR4 board using 0.5 sq. in pad size.

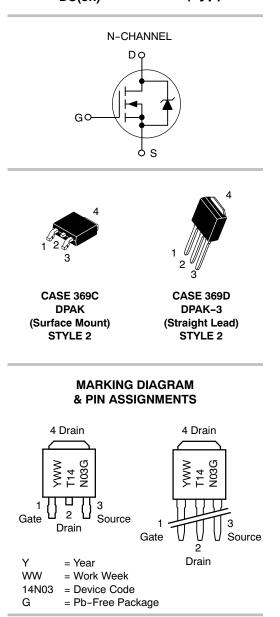
When surface mounted to an FR4 board using minimum recommended pad size.



## **ON Semiconductor®**

http://onsemi.com

## 14 AMPERES, 25 VOLTS $R_{DS(on)} = 70.4 \text{ m}\Omega$ (Typ)



**ORDERING INFORMATION** 

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

### **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise specified)

Characteristics			Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage (Note 3) (V <sub>GS</sub> = 0 Vdc, I <sub>D</sub> = 250 μAdc) Temperature Coefficient (Positive)		V(br) <sub>DSS</sub>	25 -	28 -		Vdc mV/°C
Zero Gate Voltage Drain Current ( $V_{DS}$ = 20 Vdc, $V_{GS}$ = 0 Vdc) ( $V_{DS}$ = 20 Vdc, $V_{GS}$ = 0 Vdc, $T_J$ = 150°C)		I <sub>DSS</sub>			1.0 10	μAdc
Gate-Body Leakage Current ( $V_{GS} = \pm 20$ Vdc, $V_{DS} = 0$ Vdc)		I <sub>GSS</sub>	-	-	±100	nAdc
ON CHARACTERISTICS (Note	e 3)					
Gate Threshold Voltage (Note 3) $(V_{DS} = V_{GS}, I_D = 250 \ \mu Adc)$ Threshold Temperature Coefficient (Negative)		V <sub>GS(th)</sub>	1.0 -	1.5 -	2.0	Vdc mV/°C
Static Drain-to-Source On-Resistance (Note 3) ( $V_{GS}$ = 4.5 Vdc, $I_D$ = 5 Adc) ( $V_{GS}$ = 10 Vdc, $I_D$ = 5 Adc)		R <sub>DS(on)</sub>		117 70.4	130 95	mΩ
Forward Transconductance (Note 3) (V <sub>DS</sub> = 10 Vdc, I <sub>D</sub> = 5 Adc)		9fs	-	7.0	-	Mhos
DYNAMIC CHARACTERISTIC	S					
Input Capacitance		C <sub>iss</sub>	-	115	-	pF
Output Capacitance	$(V_{DS}$ = 20 Vdc, $V_{GS}$ = 0 V, f = 1 MHz)	C <sub>oss</sub>	-	62	-	
Transfer Capacitance		C <sub>rss</sub>	-	33	-	
SWITCHING CHARACTERIST	ICS (Note 4)					
Turn-On Delay Time		t <sub>d(on)</sub>	-	3.8	-	ns
Rise Time	(V <sub>GS</sub> = 10 Vdc, V <sub>DD</sub> = 10 Vdc,	t <sub>r</sub>	-	27	-	
Turn-Off Delay Time	$I_D = 5 \text{ Adc}, \text{ R}_G = 3 \Omega$ )	t <sub>d(off)</sub>	-	9.6	-	
Fall Time		t <sub>f</sub>	-	2.0	-	
Gate Charge		QT	-	1.8	-	nC
	$(V_{GS} = 5 \text{ Vdc}, I_D = 5 \text{ Adc}, V_{DS} = 10 \text{ Vdc})$ (Note 3)	Q <sub>1</sub>	-	0.8	-	
		Q <sub>2</sub>	-	0.7	-	
SOURCE-DRAIN DIODE CHA	RACTERISTICS					
Forward On-Voltage	(I <sub>S</sub> = 5 Adc, V <sub>GS</sub> = 0 Vdc) (Note 3) (I <sub>S</sub> = 5 Adc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 125°C)	V <sub>SD</sub>		0.93 0.82	1.2 -	V <sub>dc</sub>
Reverse Recovery Time		t <sub>rr</sub>	-	6.6	-	ns
	(I <sub>S</sub> = 5 Adc, V <sub>GS</sub> = 0 Vdc,	t <sub>a</sub>	-	4.75	-	
	$dI_{S}/dt = 100 \text{ A}/\mu\text{s}$ (Note 3)	t <sub>b</sub>	-	1.88	-	

Reverse Recovery Stored Charge

Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
Switching characteristics are independent of operating junction temperatures.

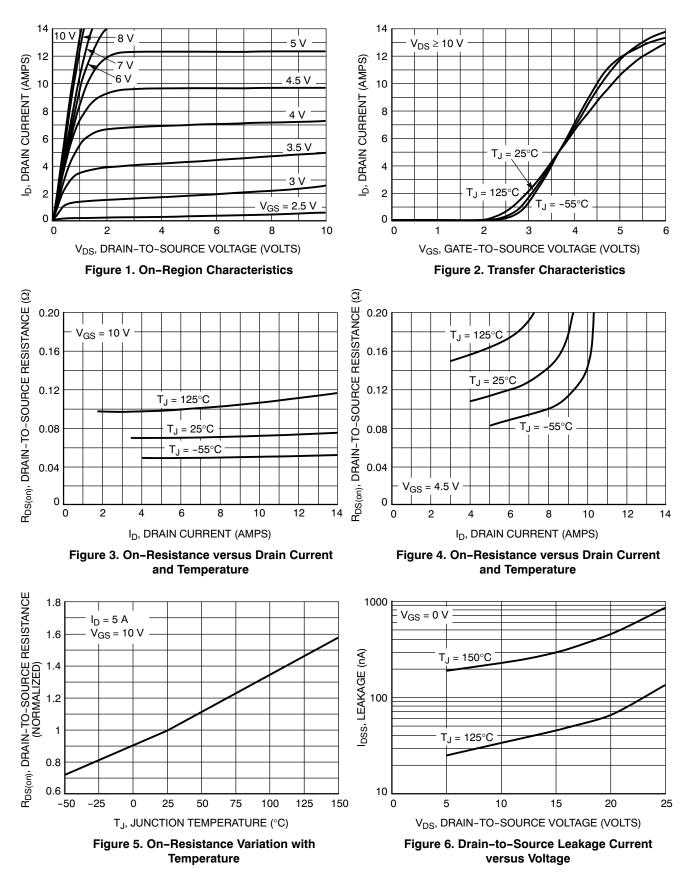
0.002

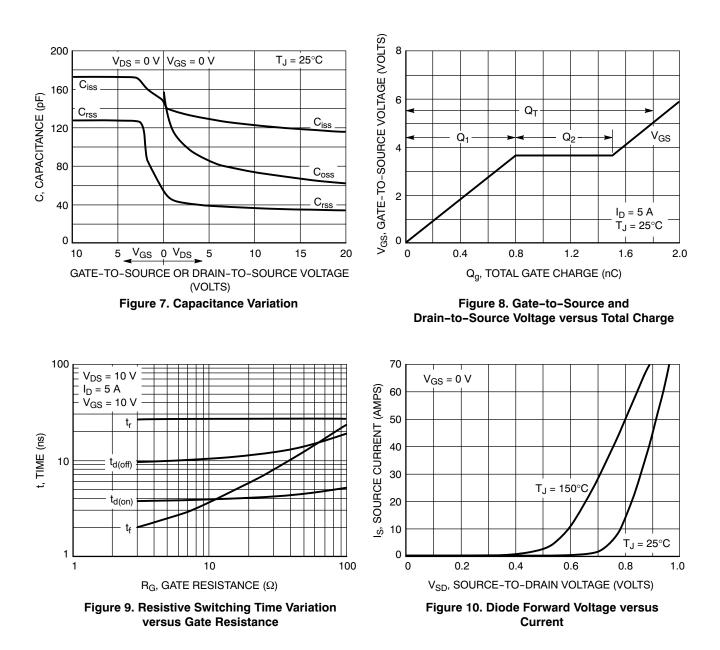
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μC

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 $\mathsf{Q}_{\mathsf{R}\mathsf{R}}$ 





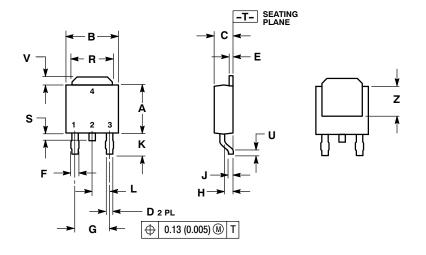
#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NTD14N03R	DPAK	75 Units / Rail
NTD14N03RG	DPAK (Pb-Free)	75 Units / Rail
NTD14N03R-001	DPAK-3	75 Units / Rail
NTD14N03R-1G	DPAK-3 (Pb-Free)	75 Units / Rail
NTD14N03RT4	DPAK	2500 Tape & Reel
NTD14N03RT4G	DPAK (Pb-Free)	2500 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### PACKAGE DIMENSIONS





1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. MILLIMETERS INCHES 
 DIM
 MIN
 MAX

 A
 0.235
 0.245
 MIN MAX 5.97 6.22 
 B
 0.235
 0.245

 B
 0.250
 0.265

 C
 0.086
 0.094

 D
 0.027
 0.035
 6.35 6.73 2.19 2.38 0.69 0.88 E0.0180.023F0.0370.045 0.46 0.58 1.14 0.94 
 G
 0.180
 BSC

 H
 0.034
 0.040

 J
 0.018
 0.023
 4.58 0.87 BSC 1.01 0.46 0.58 K 0.102 0.114 2.60 2.89 L 0.090 BSC R 0.180 0.215 S 0.025 0.040 2.29 BSC

4.57 5.45 0.63 1.01

1.27

0.63

0.51

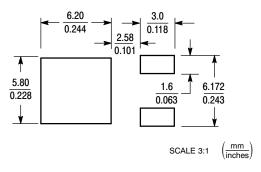
 
 V
 0.035
 0.050
 0.89

 Z
 0.155
 -- 3.93
 STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN

**U** 0.020

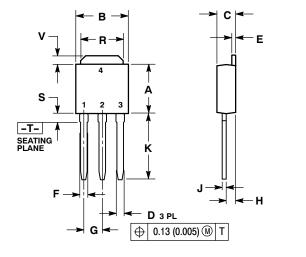
NOTES:

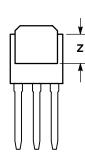
#### **SOLDERING FOOTPRINT\***

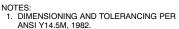


\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DPAK-3 (SINGLE GAUGE / SRAIGHT LEAD) CASE 369D-01 ISSUE B







CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
Е	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
К	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Ζ	0.155		3.93	

STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN

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